

P4C164/P4C164L ULTRA HIGH SPEED 8K x 8 STATIC CMOS RAMS



FEATURES

- Full CMOS, 6T Cell
- High Speed (Equal Access and Cycle Times)
 - 8/10/12/15/20/25 ns (Commercial)
 - 10/12/15/20/25/35 (Industrial)
 - 12/15/20/25/35/45 ns (Military)
- Low Power Operation
 - 770mW Active –15
 - 660/743 mW Active – 20
 - 495/575 mW Active – 25, 35, 45
 - 193/220 mW Standby (TTL Input)
 - 5.5mW Standby (CMOS Input) P4C164L (Military)
- Output Enable and Dual Chip Enable Control Functions
- Single 5V±10% Power Supply
- Data Retention with 2.0V Supply, 10 µA Typical Current (P4C164L Military)
- Common Data I/O
- Fully TTL Compatible Inputs and Outputs
- Standard Pinout (JEDEC Approved)
 - 28-Pin 300 mil DIP, SOJ
 - 28-Pin 600 mil Ceramic DIP
 - 28-Pin 350 x 550 mil LCC
 - 28-Pin CERPACK



DESCRIPTION

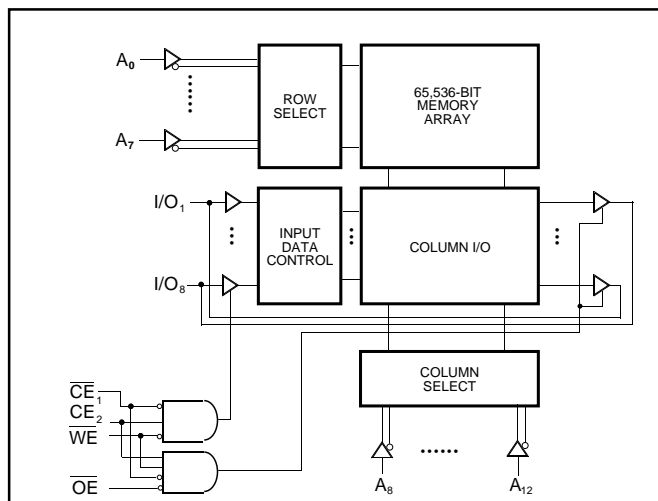
The P4C164 and P4C164L are 65,536-bit ultra high-speed static RAMs organized as 8K x 8. The CMOS memories require no clocks or refreshing and have equal access and cycle times. Inputs are fully TTL-compatible. The RAMs operate from a single 5V±10% tolerance power supply. With battery backup, data integrity is maintained with supply voltages down to 2.0V. Current drain is typically 10 µA from a 2.0V supply.

Access times as fast as 10 nanoseconds are available, permitting greatly enhanced system operating speeds. In full standby mode with CMOS inputs, power consumption is only 5.5 mW for the P4C164L.

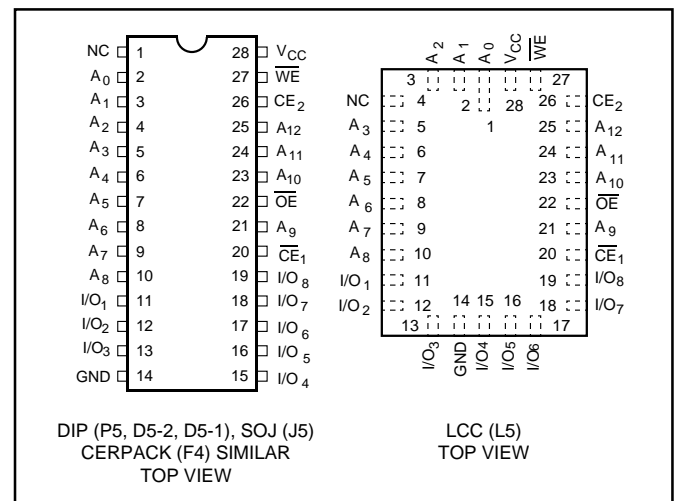
The P4C164 and P4C164L are available in 28-pin 300 mil DIP and SOJ, 28-pin 600 mil ceramic DIP, and 28-pin 350 x 550 mil LCC packages providing excellent board level densities.



FUNCTIONAL BLOCK DIAGRAM



PIN CONFIGURATIONS



Means Quality, Service and Speed

MAXIMUM RATINGS⁽¹⁾

Symbol	Parameter	Value	Unit
V_{CC}	Power Supply Pin with Respect to GND	-0.5 to +7	V
V_{TERM}	Terminal Voltage with Respect to GND (up to 7.0V)	-0.5 to $V_{CC} + 0.5$	V
T_A	Operating Temperature	-55 to +125	°C

RECOMMENDED OPERATING TEMPERATURE AND SUPPLY VOLTAGE

Grade(2)	Ambient Temperature	GND	V_{CC}
Military	-55°C to +125°C	0V	5.0V ± 10%
Industrial	-40°C to +85°C	0V	5.0V ± 10%
Commercial	0°C to +70°C	0V	5.0V ± 10%

Symbol	Parameter	Value	Unit
T_{BIAS}	Temperature Under Bias	-55 to +125	°C
T_{STG}	Storage Temperature	-65 to +150	°C
P_T	Power Dissipation	1.0	W
I_{OUT}	DC Output Current	50	mA

CAPACITANCES⁽⁴⁾

$V_{CC} = 5.0V$, $T_A = 25^\circ C$, $f = 1.0MHz$

Symbol	Parameter	Conditions	Typ.	Unit
C_{IN}	Input Capacitance	$V_{IN} = 0V$	5	pF
C_{OUT}	Output Capacitance	$V_{OUT} = 0V$	7	pF

DC ELECTRICAL CHARACTERISTICS

Over recommended operating temperature and supply voltage⁽²⁾

Symbol	Parameter	Test Conditions	P4C164		P4C164L		Unit
			Min	Max	Min	Max	
V_{IH}	Input High Voltage		2.2	$V_{CC} + 0.5$	2.2	$V_{CC} + 0.5$	V
V_{IL}	Input Low Voltage		-0.5 ⁽³⁾	0.8	-0.5 ⁽³⁾	0.8	V
V_{HC}	CMOS Input High Voltage		$V_{CC} - 0.2$	$V_{CC} + 0.5$	$V_{CC} - 0.2$	$V_{CC} + 0.5$	V
V_{LC}	CMOS Input Low Voltage		-0.5 ⁽³⁾	0.2	-0.5 ⁽³⁾	0.2	V
V_{CD}	Input Clamp Diode Voltage	$V_{CC} = \text{Min.}, I_{IN} = 18 \text{ mA}$		-1.2		-1.2	V
V_{OL}	Output Low Voltage (TTL Load)	$I_{OL} = +8 \text{ mA}, V_{CC} = \text{Min.}$		0.4		0.4	V
V_{OH}	Output High Voltage (TTL Load)	$I_{OH} = -4 \text{ mA}, V_{CC} = \text{Min.}$	2.4		2.4		V
I_{LI}	Input Leakage Current	$V_{CC} = \text{Max.}$ Mil.	-10	+10	-5	+5	μA
		$V_{IN} = \text{GND to } V_{CC}$ Com'l.	-5	+5	n/a	n/a	
I_{LO}	Output Leakage Current	$V_{CC} = \text{Max.}, \overline{CE} = V_{IH}$ Mil.	-10	+10	-5	+5	μA
		$V_{OUT} = \text{GND to } V_{CC}$ Com'l.	-5	+5	n/a	n/a	
I_{SB}	Standby Power Supply Current (TTL Input Levels)	$\overline{CE} \geq V_{IH}$ or Mil.	—	40	—	40	mA
		$CE_2 \leq V_{IL}, V_{CC} = \text{Max}$ Ind./Com'l.	—	30	—	n/a	
I_{SB1}	Standby Power Supply Current (CMOS Input Levels)	$\overline{CE} \geq V_{HC}$ or Mil.	—	25	—	1	mA
		$CE_2 \leq V_{LC}, V_{CC} = \text{Max}$ Ind./Com'l.	—	15	—	n/a	
		$f = 0$, Outputs Open					
		$V_{IN} \leq V_{LC}$ or $V_{IN} \geq V_{HC}$					

n/a = Not Applicable

Notes:

- Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to MAXIMUM rating conditions for extended periods may affect reliability.
- Extended temperature operation guaranteed with 400 linear feet per minute of air flow.
- Transient inputs with V_{IL} and I_{IL} not more negative than -3.0V and -100mA, respectively, are permissible for pulse widths up to 20ns.
- This parameter is sampled and not 100% tested.

POWER DISSIPATION CHARACTERISTICS VS. SPEED

Symbol	Parameter	Temperature Range	-8	-10	-12	-15	-20	-25	-35	-45	Unit
			Commercial	Industrial	Military	Commercial	Industrial	Military	Commercial	Industrial	
I_{CC}	Dynamic Operating Current*	Commercial	200	180	170	160	155	150	N/A	N/A	mA
		Industrial	N/A	190	180	170	160	155	150	N/A	mA
		Military	N/A	N/A	180	170	160	155	150	145	mA

* $V_{CC} = 5.5V$. Tested with outputs open. $f = \text{Max}$. Switching inputs are 0V and 3V. $\overline{CE}_1 = V_{IL}$, $CE_2 = V_{IH}$, $\overline{OE} = V_{IH}$

DATA RETENTION CHARACTERISTICS (P4C164L, Military Temperature Only)

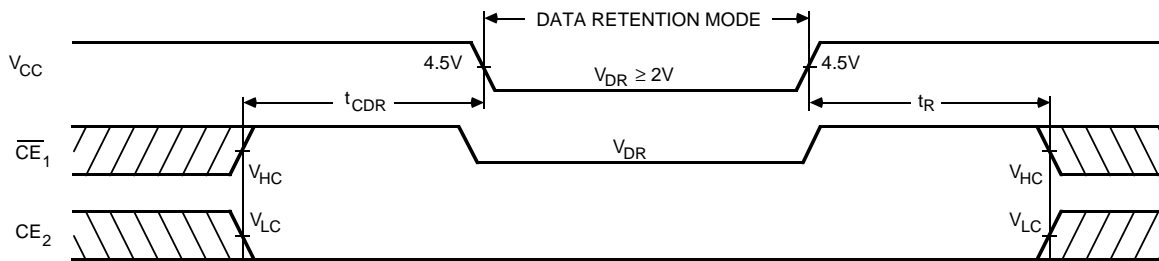
Symbol	Parameter	Test Condition	Min	Typ.*		Max		Unit
				$V_{CC} = 2.0V$	$V_{CC} = 3.0V$	$V_{CC} = 2.0V$	$V_{CC} = 3.0V$	
V_{DR}	V_{CC} for Data Retention		2.0					V
I_{CCDR}	Data Retention Current	$\overline{CE}_1 \geq V_{CC} - 0.2V$ or $CE_2 \leq 0.2V$, $V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq 0.2V$		10	15	200	300	μA
t_{CDR}	Chip Deselect to Data Retention Time		0					ns
t_R^\dagger	Operation Recovery Time		t_{RC}^\S					ns

* $T_A = +25^\circ C$

$^\S t_{RC}$ = Read Cycle Time

† This parameter is guaranteed but not tested.

DATA RETENTION WAVEFORM



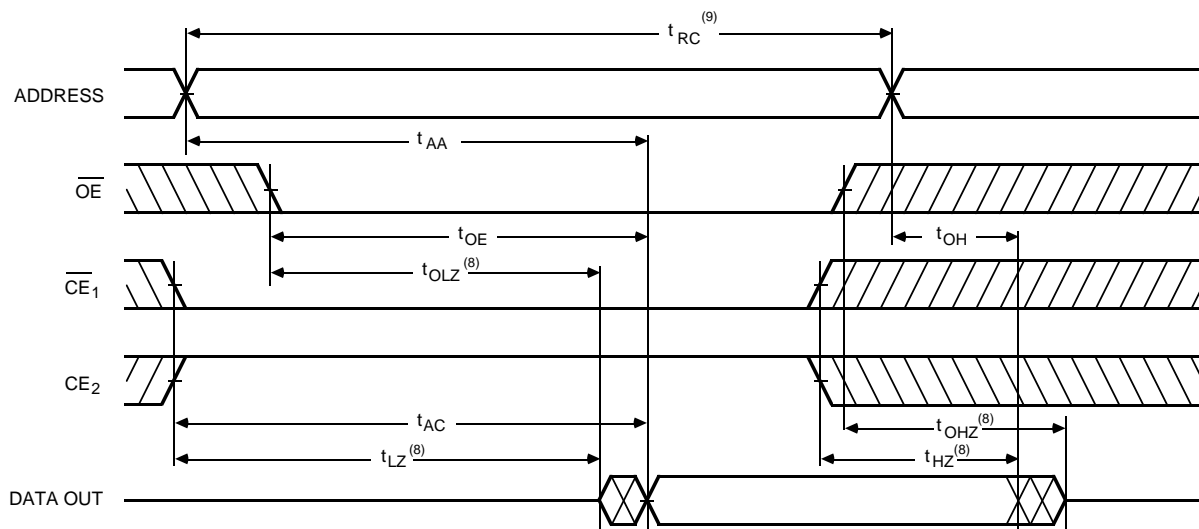


AC ELECTRICAL CHARACTERISTICS—READ CYCLE

($V_{CC} = 5V \pm 10\%$, All Temperature Ranges)⁽²⁾

Sym.	Parameter	-8		-10		-12		-15		-20		-25		-35		-45		Unit
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
t_{RC}	Read Cycle Time	8		10		12		15		20		25		35		45		ns
t_{AA}	Address Access Time		8		10		12		15		20		25		35		45	ns
t_{AC}	Chip Enable Access Time		8		10		12		15		20		25		35		45	ns
t_{OH}	Output Hold from Address Change	3		3		3		3		3		3		3		3		ns
t_{LZ}	Chip Enable to Output in Low Z	2		2		2		2		2		2		2		2		ns
t_{HZ}	Chip Disable to Output in High Z		5		6		7		8		8		10		15		20	ns
t_{OE}	Output Enable Low to Data Valid		5		6		7		9		10		13		18		20	ns
t_{OLZ}	Output Enable Low to Low Z	2		2		2		2		2		2		2		2		ns
t_{OHZ}	Output Enable High to High Z		5		6		7		9		9		12		15		20	ns
t_{PU}	Chip Enable to Power Up Time	0		0		0		0		0		0		0		0		ns
t_{PD}	Chip Disable to Power Down Time		8		10		12		15		20		20		20		25	ns

READ CYCLE NO. 1 (\overline{OE} CONTROLLED)⁽⁵⁾

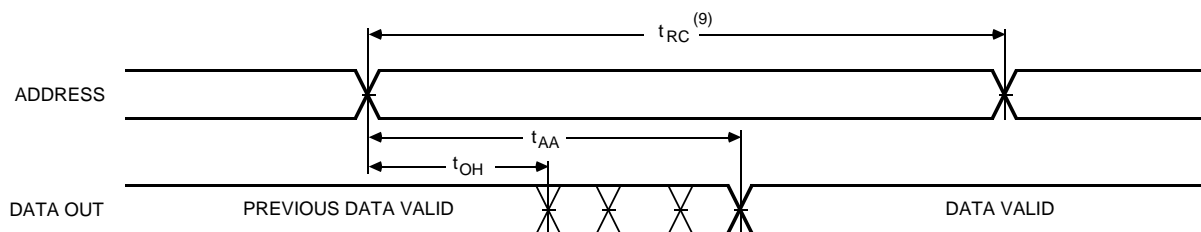


Notes:

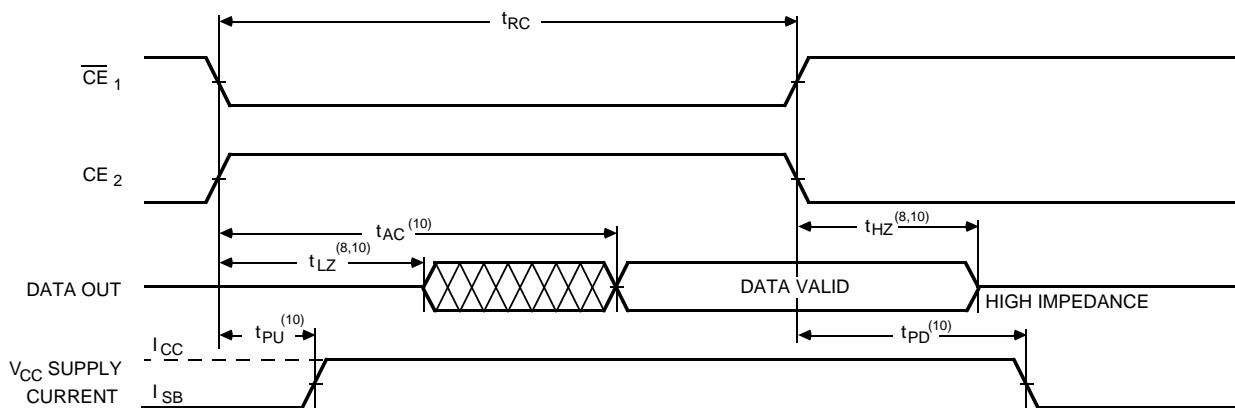
- \overline{WE} is HIGH for READ cycle.
- \overline{CE}_1 is LOW, \overline{CE}_2 is HIGH and \overline{OE} is LOW for READ cycle.
- ADDRESS must be valid prior to, or coincident with \overline{CE}_1 transition LOW and \overline{CE}_2 transition HIGH.

- Transition is measured ± 200 mV from steady state voltage prior to change, with loading as specified in Figure 1. This parameter is sampled and not 100% tested.

READ CYCLE NO. 2 (ADDRESS CONTROLLED)^(5,6)



READ CYCLE NO. 3 (\overline{CE}_1 , CE_2 CONTROLLED)^(5,7,10)



Notes:

9. READ Cycle Time is measured from the last valid address to the first transitioning address.

10. Transitions caused by a chip enable control have similar delays irrespective of whether \overline{CE}_1 or CE_2 causes them.

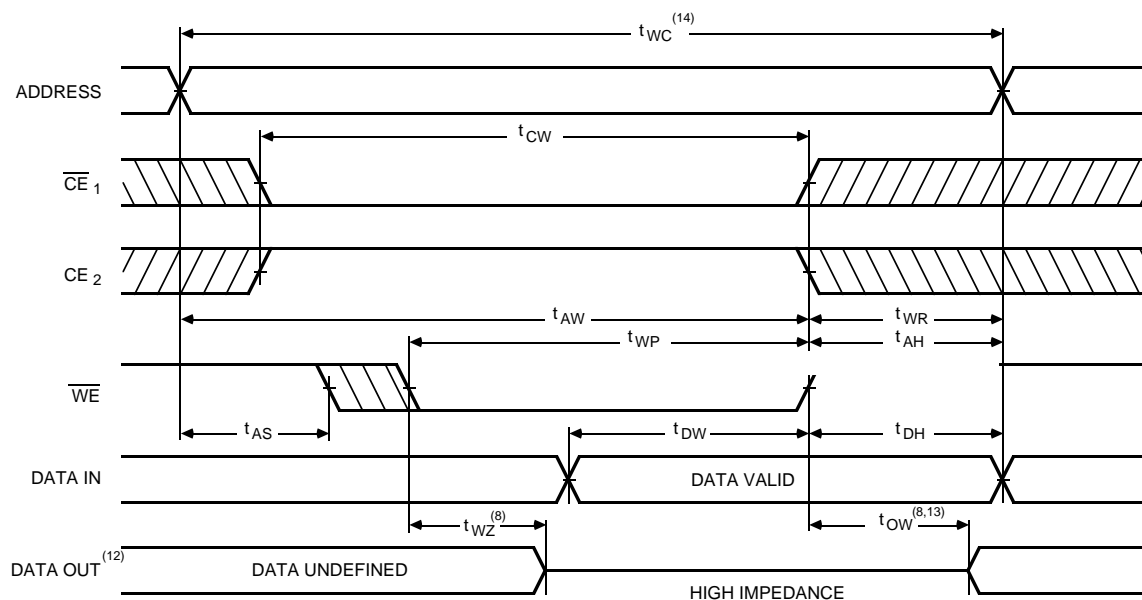


AC CHARACTERISTICS—WRITE CYCLE

($V_{CC} = 5V \pm 10\%$, All Temperature Ranges)⁽²⁾

Sym.	Parameter	-8		-10		-12		-15		-20		-25		-35		-45		Unit
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
t_{WC}	Write Cycle Time	8		10		12		15		20		25		35		45		ns
t_{CW}	Chip Enable Time to End of Write	6		7		8		12		15		18		25		33		ns
t_{AW}	Address Valid to End of Write	7		8		10		12		15		18		25		33		ns
t_{AS}	Address Set-up Time	0		0		0		0		0		0		0		0		ns
t_{WP}	Write Pulse Width	7		8		9		12		15		18		20		25		ns
t_{AH}	Address Hold Time	0		0		0		0		0		0		0		0		ns
t_{DW}	Data Valid to End of Write	6		7		8		9		11		13		15		20		ns
t_{DH}	Date Hold Time	0		0		0		0		0		0		0		0		ns
t_{WZ}	Write Enable to Output in High Z		6		7		7		7		8		10		14		18	ns
t_{OW}	Output Active from End of Write	3		3		3		3		3		3		3		3		ns

WRITE CYCLE NO. 1 (\overline{WE} CONTROLLED)⁽¹¹⁾

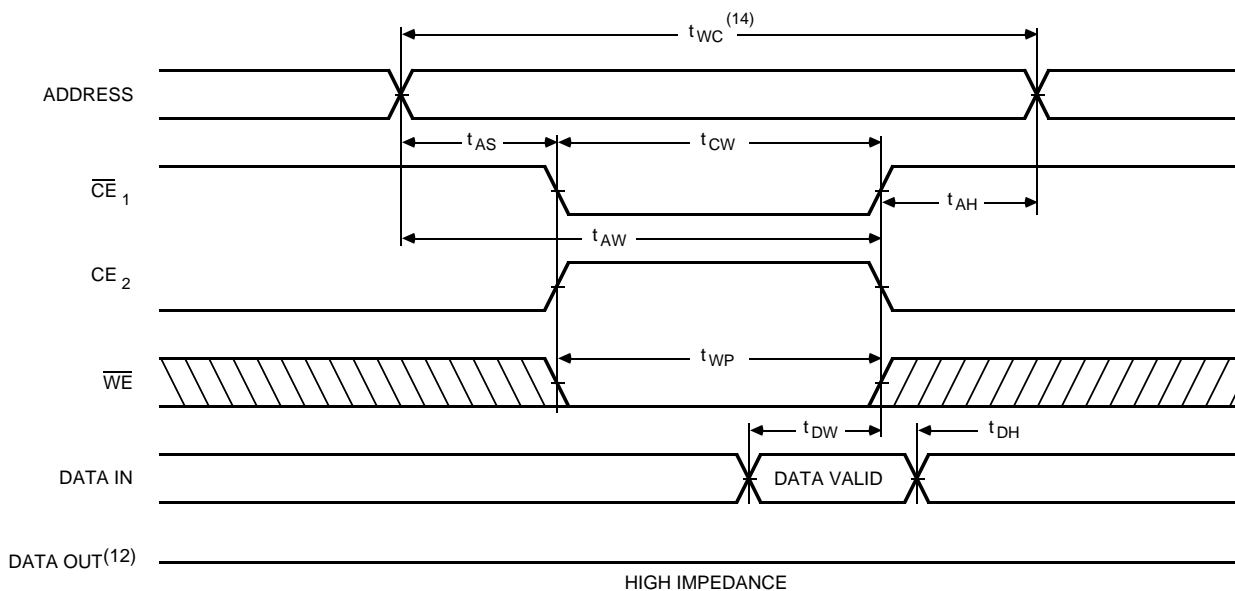


Notes:

- \overline{CE}_1 and \overline{WE} must be LOW, and \overline{CE}_2 HIGH for WRITE cycle.
- \overline{OE} is LOW for this WRITE cycle to show t_{WZ} and t_{OW} .
- If \overline{CE}_1 goes HIGH, or \overline{CE}_2 goes LOW, simultaneously with \overline{WE} HIGH, the output remains in a high impedance state.

- Write Cycle Time is measured from the last valid address to the first transitioning address.

TIMING WAVEFORM OF WRITE CYCLE NO. 2 (\overline{CE} CONTROLLED)⁽¹¹⁾



AC TEST CONDITIONS

Input Pulse Levels	GND to 3.0V
Input Rise and Fall Times	3ns
Input Timing Reference Level	1.5V
Output Timing Reference Level	1.5V
Output Load	See Figures 1 and 2

TRUTH TABLE

Mode	\overline{CE}_1	CE_2	\overline{OE}	\overline{WE}	I/O	Power
Standby	H	X	X	X	High Z	Standby
Standby	X	L	X	X	High Z	Standby
D_{OUT} Disabled	L	H	H	H	High Z	Active
Read	L	H	L	H	D_{OUT}	Active
Write	L	H	X	L	High Z	Active

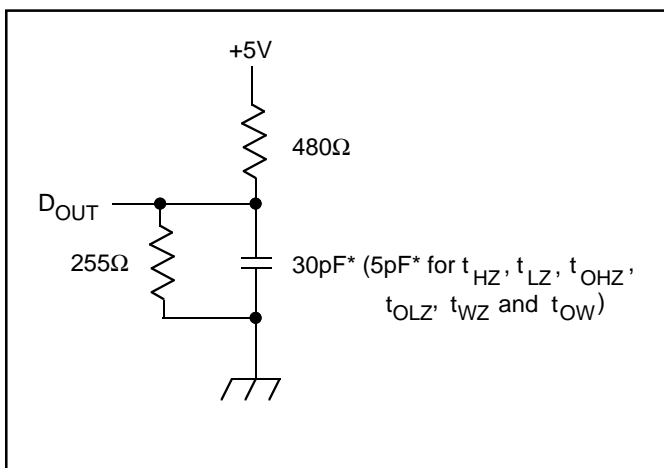


Figure 1. Output Load

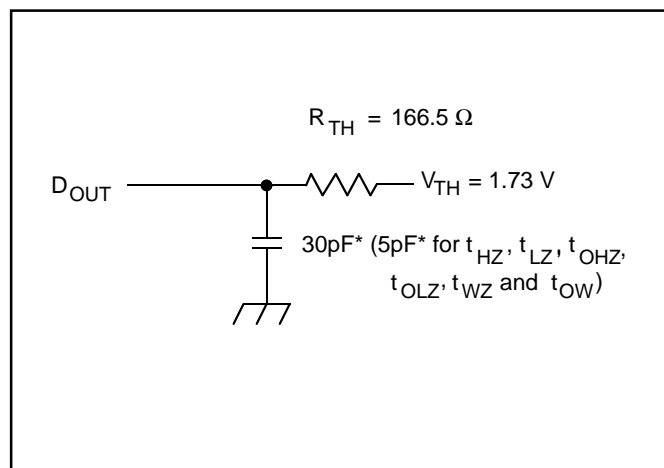


Figure 2. Thevenin Equivalent

* including scope and test fixture.

Note:

Because of the ultra-high speed of the P4C164/L, care must be taken when testing this device; an inadequate setup can cause a normal functioning part to be rejected as faulty. Long high-inductance leads that cause supply bounce must be avoided by bringing the V_{CC} and ground planes directly up to the contactor fingers. A 0.01 μ F high frequency capacitor is also required between V_{CC} and ground. To avoid signal

reflections, proper termination must be used; for example, a 50 Ω test environment should be terminated into a 50 Ω load with 1.73V (Thevenin Voltage) at the comparator input, and a 116 Ω resistor must be used in series with D_{OUT} to match 166 Ω (Thevenin Resistance).



PACKAGE SUFFIX

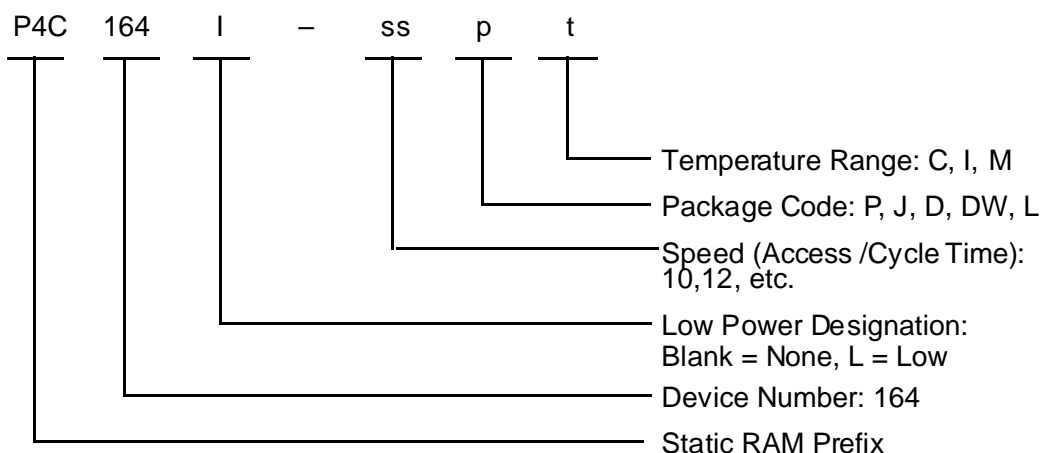
Package Suffix	Description
P	Plastic DIP, 300 mil wide standard
J	Plastic SOJ, 300 mil wide standard
D	CERDIP, 300 mil wide
DW	CERDIP, 600 mil wide
L	Leadless Chip Carrier (ceramic)
F	CERPACK

TEMPERATURE RANGE SUFFIX

Temperature Range Suffix	Description
C	Commercial Temperature Range, 0°C to +70°C.
I	Industrial Temperature Range, -40°C to +85°C.
M	Military Temperature Range, -55°C to +125°C.
MB	Mil. Temp. with MIL-STD-883 Class B compliance.

ORDERING INFORMATION

Performance Semiconductor's part numbering scheme is as follows:



The P4C164 is also available to SMD-5962-38294

SELECTION GUIDE

The P4C164 is available in the following temperature, speed and package options. The P4C164L is available only over the military temperature range.

Temp. Range	Package	Speed							
		8	10	12	15	20	25	35	45
Com'l	Plastic DIP	-8PC	-10PC	-12PC	-15PC	-20PC	-25PC	N/A	N/A
	Plastic SOJ	-8JC	-10JC	-12JC	-15JC	-20JC	-25JC	N/A	N/A
Ind.	Plastic DIP	N/A	-10PI	-12PI	-15PI	-20PI	-25PI	-35PI	N/A
	Plastic SOJ	N/A	-10JI	-12JI	-15JI	-20JI	-25JI	-35JI	N/A
Mil. Temp.	CERDIP (300 mil)	N/A	N/A	-12DM	-15DM	-20DM	-25DM	-35DM	-45DM
	CERDIP (600 mil)	N/A	N/A	-12DWM	-15DWM	-20DWM	-25DWM	-35DWM	-45DWM
	LCC	N/A	N/A	-12LM	-15LM	-20LM	-25LM	-35LM	-45LM
	CERPACK	N/A	N/A	-12FM	-15FM	-20FM	-25FM	-35FM	-45FM
Military Proc'd*	CERDIP (300 mil)	N/A	N/A	-12DMB	-15DMB	-20DDMB	-25DMB	-35DMB	-45DMB
	CERDIP (600 mil)	N/A	N/A	-12DWMB	-15DWMB	-20DWMB	-25DWMB	-35DWMB	-45DWMB
	LCC	N/A	N/A	-12LMB	-15LMB	-20LMB	-25LMB	-35LMB	-45LMB
	CERPACK	N/A	N/A	-12FMB	-15FMB	-20FMB	-25FMB	-35FMB	-45FMB

* Military temperature range with MIL-STD-883, Class B processing.

N/A = Not available